

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-10. (Canceled).

11. (Currently Amended) A scanning exposure method for scanning and exposing a pattern of a mask in a predetermined direction multiple times and transferring a desired pattern onto a substrate by stitching the pattern multiple times, the method comprising:

~~scanning a pattern region of the mask by an illumination region defined by an aperture stop~~ the mask and the substrate in the predetermined direction synchronously with illumination light of an illumination region defined by an aperture stop which illuminates a pattern region of the mask to project the pattern onto the substrate; and

~~stitching the patterns adjacent to each other in the scanning direction by controlling an exposure amount of a stitching region to form the desired pattern.~~

in order to overlap patterns adjacent to each other in a scanning direction on the substrate to form the desired pattern, stitching the patterns by controlling an aperture shape of the aperture stop to control an exposure amount distribution in the predetermined direction in a stitching region which extends toward a direction intersecting the predetermined direction and in which the patterns are overlapped.

12. (Previously Presented) A scanning exposure method as recited in claim 11, wherein

an exposure amount of the stitching region is controlled by changing a width in the scanning direction of the aperture stop of the illumination region which illuminates the mask.

13. (Previously Presented) A scanning exposure method as recited in claim 11, wherein

at a starting time and at an ending time of the scanning and exposing of the pattern region of the mask, an opening operation and a closing operation of the aperture stop are performed synchronously with the scanning and exposing.

14. (Currently Amended) A scanning exposure method as recited in claim 11, wherein

an exposure amount of the stitching region is controlled by controlling a light amount of the illumination light which illuminates the mask.

15. (Currently Amended) A scanning exposure method as recited in claim 11, wherein

the stitching of the patterns of the mask is performed by partially overlapping patterns formed to be adjacent to each other in a the direction which intersects with the scanning direction.

16. (Previously Presented) A scanning exposure method as recited in claim 11, wherein

the scanning and exposing is performed with a projection optical system which transfers the pattern of the mask and that is provided between the mask and the substrate, and with a correcting plate which corrects a predetermined image-forming characteristic and that is disposed in the projection optical system.

17. (Previously Presented) A scanning exposure method as recited in claim 11, wherein

the scanning and exposing is performed in order for an exposure amount of the partially overlapped region to have an exposure amount distribution of a trapezoidal shape in which the exposure amount becomes lower toward outer sides of the pattern of each mask to be exposed.

18. (Previously Presented) A scanning exposure method as recited in claim 11,
wherein
a projection optical system which transfers the pattern of the mask is provided
between the mask and the substrate and the pattern of the mask is scanned and exposed onto
the substrate by an approximately 1:1 magnification.